

HD74LVC2G66

2-channel Analog Switch

REJ03D0024-0300 Rev.3.00 Jul.07.2005

Description

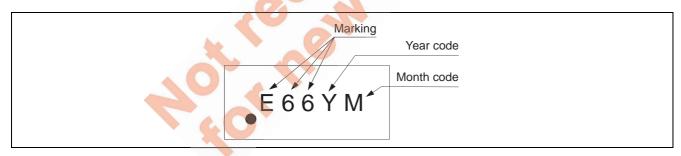
The HD74LVC2G66 has 2—channel analog switch in an 8-pin package. Each switch section has its own enable input control (CONT). High-level voltage applied to CONT turns on associated switch section. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

Features

- The basic gate function is lined up as renesas uni logic series.
- Supply voltage range: 1.65 to 5.5 V
- Operating temperature range: -40 to +85°C
- Control inputs: V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V)
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LVC2G66CPE	WCSP-8 pin	SXBG0008KA-A (TBS-8V)	СР	E (3,000 pcs/reel)
HD74LVC2G66CLE	1 VVCOI -0 PIII	SXBG0008KB-A (TBS-8AV)	CL	L (3,000 pcs/reel)

Article Indication

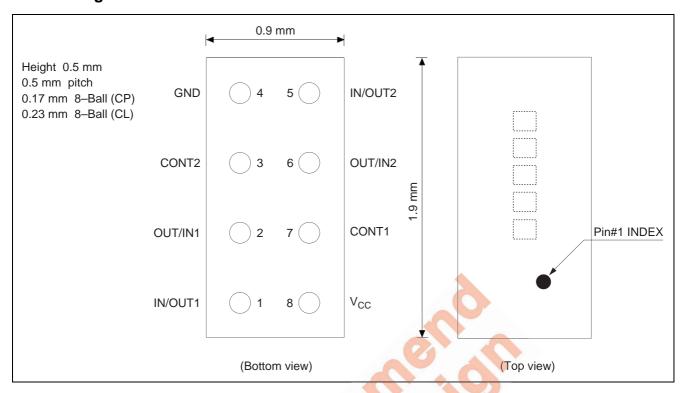


Function Table

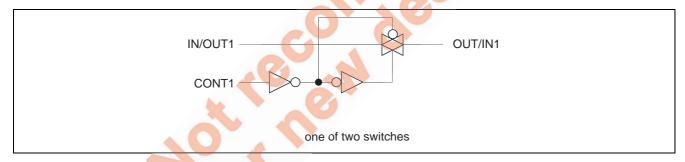
Control	Switch				
L	OFF				
Н	ON				

H : High level L : Low level

Pin Arrangement



Logic Diagram



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V _{CC}	-0.5 to 6.5	V	
Input voltage range *1	Vı	-0.5 to 6.5	V	
Output voltage range *1, 2	Vo	-0.5 to V_{CC} +0.5	V	Output : H or L
Input clamp current	I _{IK}	- 50	mA	V _I < 0
Output clamp current	I _{OK}	– 50	mA	V _O < 0
Continuous output current	lo	±50	mA	$V_O = 0$ to V_{CC}
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±100	mA	
Package Thermal impedance	θ_{ja}	140	°C/W	СР
		102		CL
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.





Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V_{CC}	1.65	5.5	V	
Input voltage range	Vı	0	5.5	V	
Output voltage range	Vo	0	V _{CC}	V	
Input transition rise or fall rate	Δt / Δν	0	20	ns / V	$V_{CC} = 1.65 \text{ to } 1.95 \text{ V},$
					2.3 to 2.7 V
		0	10		$V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$
		0	10		$V_{CC} = 4.5 \text{ to } 5.5 \text{ V}$
Operating free-air temperature	Ta	-40	85	°C	

Note: Unused or floating inputs must be held high or low.



Electrical Characteristics

• $Ta = -40 \text{ to } 85^{\circ}\text{C}$

Item	Symbol	V _{CC} (V)	Min	Тур	Max	Unit	Test condition
Input voltage	V _{IH}	1.65 to 1.95	V _{CC} ×0.65	_	_	V	
		2.3 to 2.7	$V_{CC} \times 0.7$				
		3.0 to 3.6	$V_{CC} \times 0.7$	_	_		
		4.5 to 5.5	V _{CC} ×0.7	_	_		
	V _{IL}	1.65 to 1.95	_	_	V _{CC} ×0.35		
		2.3 to 2.7	_	_	V _{CC} ×0.3		
		3.0 to 3.6	_	_	V _{CC} ×0.3		
		4.5 to 5.5	_	_	V _{CC} ×0.3		
On-state switch	R _{ON}	1.65	_	12.5	30	Ω	I _S = 4 mA
resistance		2.3	_	9	20		I _S = 8 mA
		3.0	_	7.5	15		$I_S = 24 \text{ mA}$ $V_{I=V_{CC}}$ or GND
		4.5	_	6	10		I _S = 32 mA
Peak on resistance	R _{ON} (P)	1.65	_	85	120		I _S = 4 mA
		2.3	_	22	30		Is = 8 mA
		3.0		12	20		$I_S = 24 \text{ mA}$ $V_{I}=V_{CC} \text{ to GND}$
		4.5	_	7.5	15		I _S = 32 mA
Difference of	ΔR_{ON}	1.65	_	- /4	7	A O	I _S = 4 mA
on-state resistance		2.3	_		5		I _S = 8 mA
between switches		3.0	_		3		$I_S = 24 \text{ mA}$ $V_{i}=V_{CC} \text{ to GND}$
		4.5	_	(A)	2		I _S = 32 mA
Off-state switch	I _{S (OFF)}	5.5	_	0-	±1.0	μΑ	$V_I = V_{CC}$ and $V_O = GND$ or
leakage current			-(0	—	±0.1*1		$V_I = GND$ and $V_O = V_{CC}$,
							$V_C = V_{IL}$
On-state switch	I _{S (ON)}	5.5		_	±1.0	μΑ	$V_I = V_{CC}$ or GND, $V_C = V_{IH}$
leakage current			V6-		±0.1* ¹		V _O = Open
Control input	I _{IN}	5.5	_		±1.0	μΑ	$V_{IN} = V_{CC}$ or GND
current) –	±0.1* ¹		
Quiescent	Icc	5.5		_	10	μΑ	$V_{IN} = V_{CC}$ or GND
supply current				_	1.0* ¹		
	Δ lcc	5.5	_	_	500	μΑ	$V_C = V_{CC}-0.6 V$
Control input	C _{IC}	5.0	_	3.5	_	pF	
capacitance		R					
Switch terminal	C _{I/O(OFF)}	5.0	_	6.0	_	pF	
capacitance	C _{I/O(ON)}	5.0	_	14.0	_		

Note: 1. Ta = 25°C

Switching Characteristics

• $V_{CC} = 1.8 \pm 0.15 \text{ V}$

		Ta = -40 to 85°C			Test	FROM	ТО
Item	Symbol	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation delay time*1	t _{PLH} , t _{PHL}	_	2.0	ns	$C_L = 30 \text{ pF}, R_L = 1.0 \text{ k}\Omega$	INOUT or	OUTIN or
						OUTIN	INOUT
Enable time	t_{ZH}, t_{ZL}	2.3	10.0		$C_L = 30 \text{ pF}, R_L = 1.0 \text{ k}\Omega$	CONT	INOUT or
							OUTIN
Disable time	t_{HZ} , t_{LZ}	2.5	10.5		$C_L = 30 \text{ pF}, R_L = 1.0 \text{ k}\Omega$	CONT	INOUT or
							OUTIN

• $V_{CC} = 2.5 \pm 0.2 \text{ V}$

		Ta = -40	to 85°C		Test	FROM	ТО
Item	Symbol	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation delay time*1	t _{PLH} , t _{PHL}	_	1.2	ns	$C_L = 30 \text{ pF}, R_L = 500 \Omega$	INOUT or	OUTIN or
						OUTIN	INOUT
Enable time	t_{ZH}, t_{ZL}	1.6	5.6		$C_L = 30 \text{ pF}, R_L = 500 \Omega$	CONT	INOUT or
							OUTIN
Disable time	t _{HZ} , t _{LZ}	1.2	6.9		$C_L = 30 \text{ pF}, R_L = 500 \Omega$	CONT	INOUT or
							OUTIN

• $V_{CC} = 3.3 \pm 0.3 \text{ V}$

		Ta = -40 to 85°C			Test	FROM	ТО
Item	Symbol	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation delay time*1	t _{PLH} , t _{PHL}	_	0.8	ns	$C_L = 50 \text{ pF}, R_L = 500 \Omega$	INOUT or	OUTIN or
						OUTIN	INOUT
Enable time	t_{ZH}, t_{ZL}	1.5	4.4		$C_L = 50 \text{ pF}, R_L = 500 \Omega$	CONT	INOUT or
							OUTIN
Disable time	t_{HZ}, t_{LZ}	2.0	7.2		$C_L = 50 \text{ pF}, R_L = 500 \Omega$	CONT	INOUT or
							OUTIN

$\bullet \quad V_{CC} = 5.0 \pm 0.5 \ V$

		Ta = −40	to 85°C		Test	FROM	ТО
Item	Symbol	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation delay time*1	t _{PLH} , t _{PHL}	-	0.6	ns	$C_L = 50 \text{ pF}, R_L = 500 \Omega$	INOUT or	OUTIN or
						OUTIN	INOUT
Enable time	t _{zH} , t _{zL}	1.3	3.9		$C_L = 50 \text{ pF}, R_L = 500 \Omega$	CONT	INOUT or
							OUTIN
Disable time	t _{HZ} , t _{LZ}	1.1	6.3		$C_L = 50 \text{ pF}, R_L = 500 \Omega$	CONT	INOUT or
							OUTIN

Notes: 1. The propagation delay is calculated RC time constant of typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

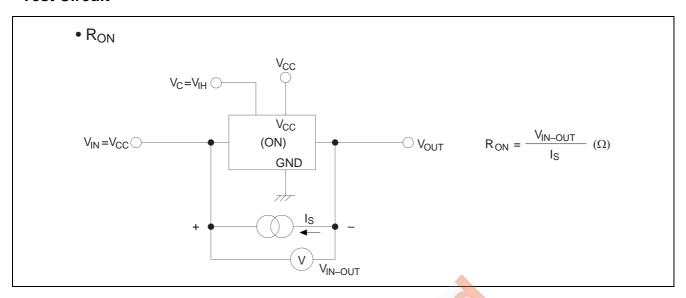
Analog Switch Characteristics

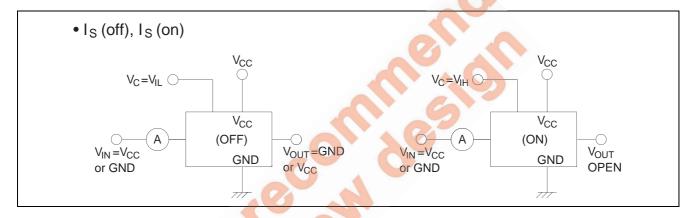
		Т	a = 25°	С				FROM	то
Item	V _{cc} (V)	Min	Тур	Max	Unit	Те	st conditions	(Input)	(Output)
Frequency response	1.65	_	35	_	MHz	$C_L = 50 \text{ pF},$	Adjust fin voltage to	INOUT or	OUTIN or
(Switch ON)	2.3		120			$R_L = 600 \Omega$	obtain 0dBm at output	OUTIN	INOUT
	3.0	_	175	_			when fin is 1MHz (sine		
	4.5		195				wave).		
	1.65	_	>300	_		$C_L = 5 pF$,	Increase fin frequency		
	2.3	_	>300	_		$R_L = 50 \Omega$	until the dB-meter reads -3 dBm.		
	3.0	_	>300	_			reads -3 dBm . 20 $\log(V_0/V_1) = -3 \text{ dBm}$		
	4.5	_	>300	_			20 log(v ₀ /v ₁)= -3 dbiii		
Crosstalk	1.65	_	- 58	_	dB	$C_L = 50 \text{ pF},$	Adjust fin voltage to	INOUT or	OUTIN or
(between switches)	2.3	_	- 58	_		$R_L = 600 \Omega$	obtain 0dBm at input	OUTIN	INOUT
	3.0	_	- 58	_			when fin is 1MHz (sine		
	4.5	_	- 58	_			wave).		
	1.65		-42			$C_L = 5 pF$,			
	2.3	_	-42	_		$R_L = 50 \Omega$			
	3.0	_	-42	_					
	4.5	_	-42	_					
Crosstalk	1.65	_	35	_	mV	$C_L = 50 \text{ pF},$	Adjust RL value to	CONT	OUTIN or
(Control input to signal	2.3		50			$R_L = 600 \Omega$	obtain 0A at I _{IN/OUT}		INOUT
output)	3.0	_	70	_			when fin is 1MHz		
	4.5	_	100	_			(square wave)		
Feed through	1.65	_	- 58	_	dB	$C_L = 50 pF$,	Adjust fin voltage to	INOUT or	OUTIN or
attenuation	2.3	_	- 58	_		$R_L = 600 \Omega$	obtain 0dBm at input	OUTIN	INOUT
(Switch OFF)	3.0	_	- 58	_			when fin is 1MHz		
	4.5	_	- 58	_			(sine-wave)		
	1.65	_	-42	-(0		$C_L = 5 pF$,			
	2.3	_	-42			$R_L = 50 \Omega$			
	3.0	_	-42			100			
	4.5		-42						
Sine-wave distortion	1.65	-	0.1	- 6	%	$C_L = 50 \text{ pF},$	$V_{I}=1.4V_{P-P}, V_{CC}=1.65V$	INOUT or	OUTIN or
	2.3	1	0.025	_($R_L = 10 \text{ k}\Omega$	$V_{I}=2.0V_{P-P}, V_{CC}=2.3V$	OUTIN	INOUT
	3.0	U	0.015	_ \		fin = 1kHz	$V_{I}=2.5V_{P-P}, V_{CC}=3.0V$		
	4.5	-	0.01			(sine-wave)	V_{I} =4.0 V_{P-P} , V_{CC} =4.5 V		
	1.65	- 8.	0.15	<u>*</u>		$C_L = 50 \text{ pF},$			
	2.3	- *	0.025	_		$R_L = 10 \text{ k}\Omega$			
	3.0	_	0.015	_		fin = 10kHz			
	4.5	_	0.01	_		(sine-wave)			

Operating Characteristics

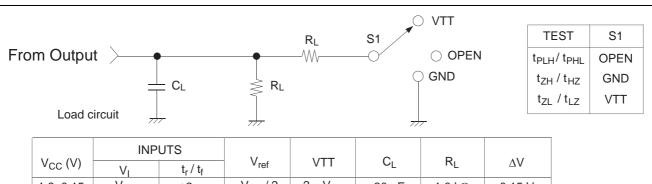
			Ta = 25°C				
ltem	Symbol	V _{CC} (V)	Min	Тур	Max	Unit	Test Conditions
Power dissipation capacitance	C_{PD}	1.8	_	8	_	pF	f = 10 MHz
		2.5		9	_		
		3.3		9.5	_		
		5.0	_	11	_		

Test Circuit

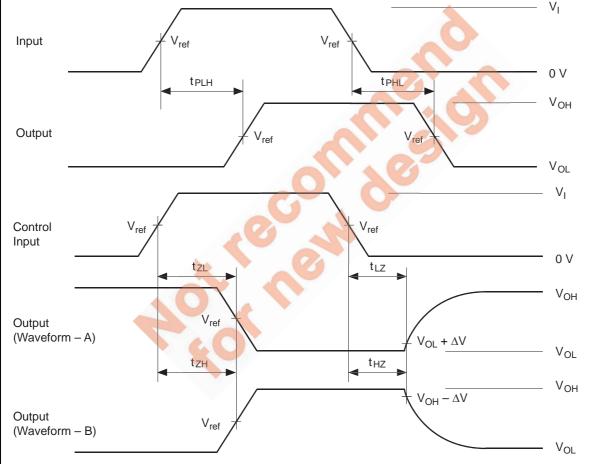




Test Circuit (cont.)

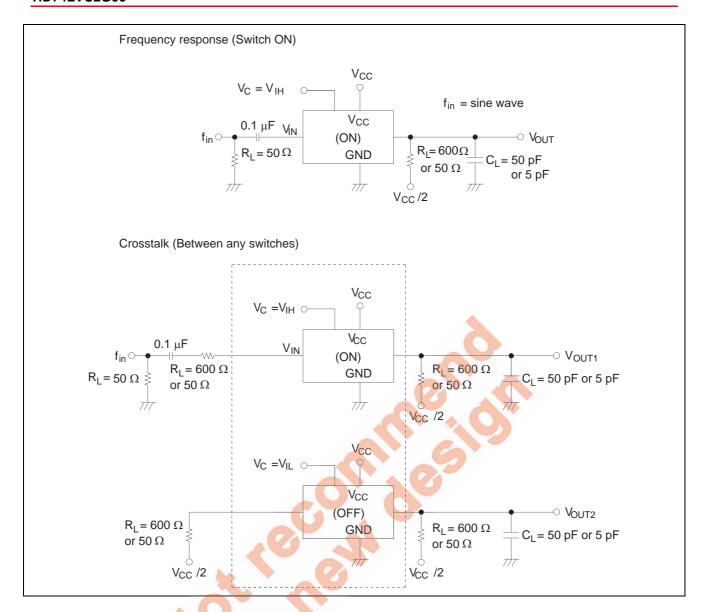


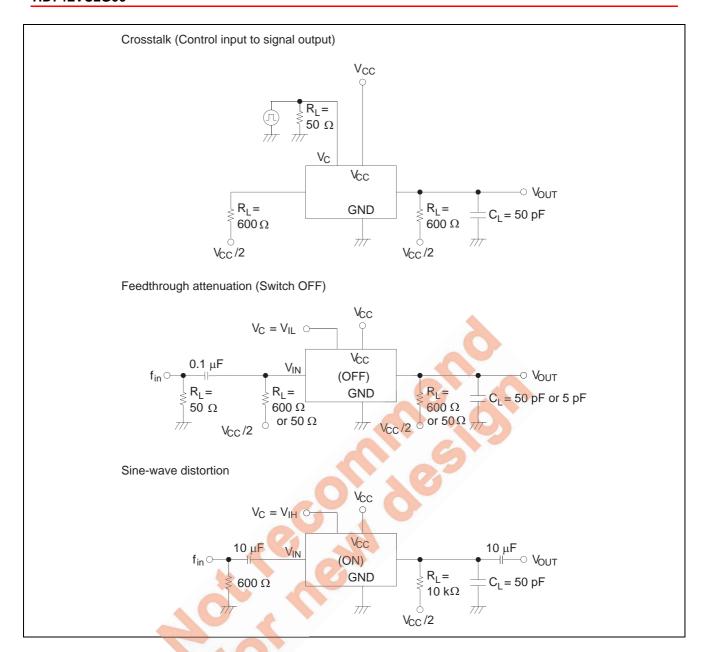
., .,	INP	UTS	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	\	0			
V _{CC} (V)	VI	t _r / t _f	V _{ref}	VTT	C_L	R _L	ΔV	
1.8±0.15	V _{CC}	≤ 2 ns	V _{CC} /2	2 × V _{CC}	30 pF	1.0 kΩ	0.15 V	
2.5±0.2	V _{CC}	≤ 2 ns	V _{CC} /2	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V	
3.3±0.3	V _{CC}	≤ 2.5 ns	V _{CC} /2	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V	
5.0±0.5	V _{CC}	≤ 2.5 ns	V _{CC} /2	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V	



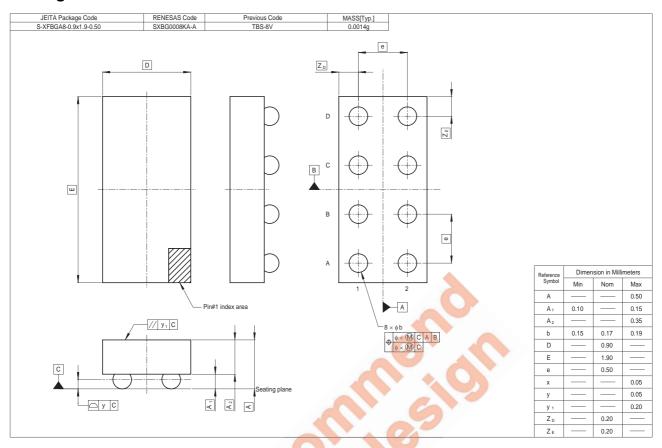
Notes: 1. C_L includes probe and jig capacitance.

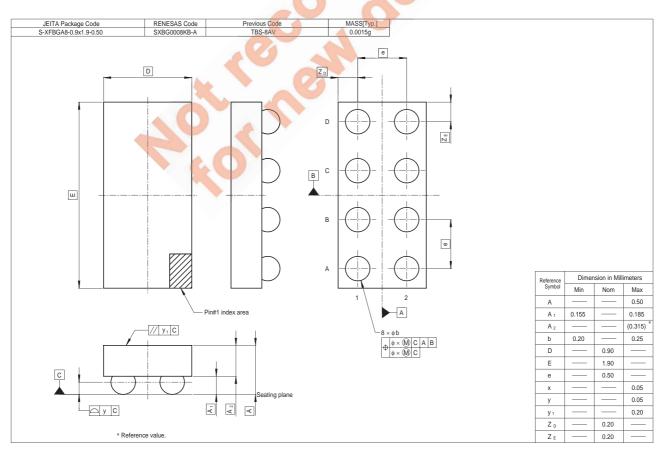
- 2. Waveform—A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform–B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. All input pulses are supplied by generators having the following characteristics: PRR \leq 10MHz, Zo = 50 $\Omega.$
- 5. The output are measured one at a time with one transition per measurement.





Package Dimensions





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